Composite Transistors

Panasonic

XN0111H (XN111H)

Silicon PNP epitaxial planar type

For switching/digital circuits

Features

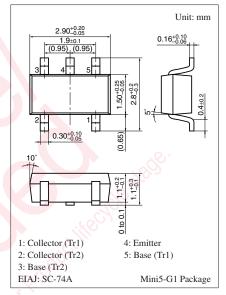
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR211H (UN211H) × 2

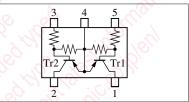
Absolute Maximum Ratings $T_a = 25^{\circ}C$

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Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	-50	V				
Collector-emitter voltage (Base open)	V _{CEO}	-50	V				
Collector current	I _C	-100	mA				
Total power dissipation	P _T	300	mW				
Junction temperature	Тј	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				



Marking Symbol: 9X

Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

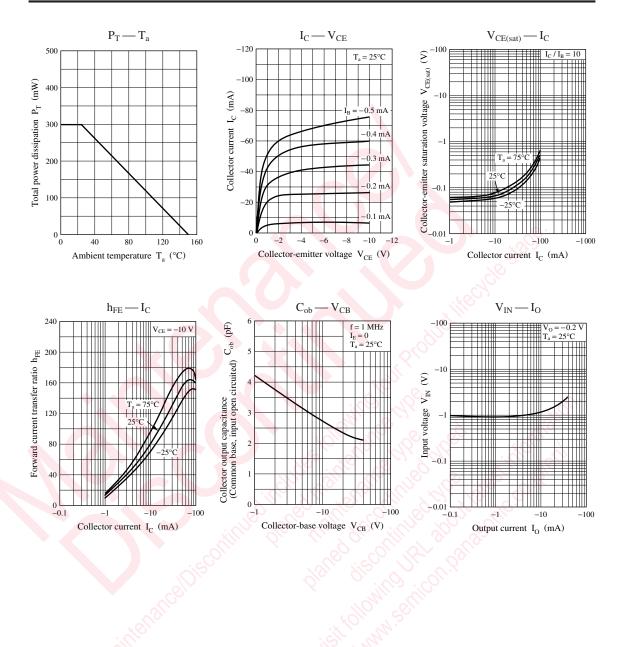
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu \text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			- 0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	30			
h _{FE} Ratio *	h _{FE(Small} /Large)	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, \text{V}_{\text{B}} = -2.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k} \Omega$			- 0.2	V
Input resistance	R ₁		-30%	2.2	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.17	0.22	0.27	
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.

XN0111H





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